IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) A pattern forming method comprising:

forming a ~~liquid-repellent thin~~ film on an insulating surface~~, the liquid-repellent thin film being repellent to a liquid composition~~;

horizontally moving a first nozzle and a second nozzle, which are integrated, to a first selected portion of the ~~liquid-repellent thin~~ film with a spacing between the integrated first nozzle and second nozzle, and the film;

irradiating the first selected portion of the ~~liquid-repellent thin~~ film with plasma from the first nozzle ~~so that the selected portion has a liquid affinity to the liquid composition~~ after the step of horizontally moving the integrated first nozzle and second nozzle; [[and]]

forming a first pattern by applying a drop of [[the]] a liquid composition to the first selected portion from the second nozzle ~~surface~~ after irradiating the first selected portion with plasma;

horizontally moving the integrated first nozzle and second nozzle to a second selected portion of the film with a spacing between the integrated first nozzle and second nozzle, and the film, after forming the first pattern;

irradiating the second selected portion of the film with plasma from the first nozzle after the step of horizontally moving the integrated first nozzle and second nozzle; and

forming a second pattern by applying a drop of the liquid composition to the second selected portion from the second nozzle after irradiating the second selected portion with plasma.

2. (Currently amended) A pattern forming method comprising:

forming a [[thin]] film ~~having an affinity for a liquid composition~~ on an insulating surface;

horizontally moving a first nozzle and a second nozzle, which are integrated, to a first selected portion of the [[thin]] film with a spacing between the integrated first nozzle and second nozzle, and the film;

selectively irradiating the first selected portion with plasma from the first nozzle to form a first groove or a first hole in a surface of the first selected portion after the step of horizontally moving the integrated first nozzle and second nozzle;

~~selectively forming a groove or a hole in a surface of the selected portion by selectively treating the selected portion with a plasma from the first nozzle; and~~

forming a first pattern by applying a drop of [[the]] a liquid composition to the first groove or the first hole in the first selected portion from the second nozzle after irradiating the first selected portion with plasma;

horizontally moving the integrated first nozzle and second nozzle to a second selected portion of the film with a spacing between the integrated first nozzle and second nozzle, and the film, after forming the first pattern;

selectively irradiating the second selected portion with plasma from the first nozzle to form a second groove or a second hole in a surface of the second selected portion after step of horizontally moving the integrated first nozzle and second nozzle; and

forming a second pattern by applying a drop of the liquid composition to the second groove or the second hole in the first selected portion from the second nozzle after irradiating the second selected portion with plasma.

3. (Previously Presented) A pattern forming method according to claim 1, wherein the liquid composition comprises at least one selected from the group consisting of a conductive material, a resist material, a polymer material and a light emitting material.

4. (Currently amended) A pattern forming method according to claim 1, wherein the ~~liquid-repellent thin~~ film is selected from the group consisting of a semiconductor film, a conductive film and a polymer film.

5. (Currently amended) A pattern forming method according to claim 2, wherein the [[thin]] film ~~having affinity for the liquid composition~~ is selected from the group consisting of a silicon oxide film, silicon nitride film, a silicon oxynitride film and a metal oxide film.

6. (Previously Presented) A pattern forming method according to claim 1, wherein the irradiation with the plasma is performed at a pressure in a range of 1.3×10^1 to 1.31×10^5 Pa.

7-15. (Canceled)

16. (Previously Presented) A pattern forming method according to claim 2, wherein the liquid composition comprises at least one selected from the group consisting of a conductive material, a resist material, a polymer material and a light emitting material.

17. (Currently amended) A pattern forming method according to claim 2, wherein the

treatment of the [[thin]] film with the plasma is performed at a pressure in a range of 1.3×10^1 to 1.31×10^5 Pa.

18-22 (Canceled).

23. (Currently amended) A pattern forming method comprising:

horizontally moving a first nozzle and a second nozzle, which are integrated, to a first selected portion of a surface with a spacing between the integrated first nozzle and second nozzle, and the surface;

irradiating the first selected portion of the surface with plasma of a gas from the first nozzle ~~so that the selected portion has a liquid affinity to a liquid composition comprising a conductive material~~ after the step of horizontally moving the integrated first nozzle and second nozzle; and

forming a first conductive pattern by applying a drop of the liquid composition to the first selected portion from the second nozzle after irradiating the first selected portion with plasma;

forming a first mask pattern of a resist over the first conductive pattern; [[and]]

forming a first wiring by etching the first conductive pattern using the first mask pattern;

horizontally moving the integrated first nozzle and second nozzle to a second selected portion of the surface with a spacing between the integrated first nozzle and second nozzle, and the surface, after forming the first wiring;

irradiating the second selected portion of the surface with plasma of a gas from the first nozzle after the step of horizontally moving the integrated first nozzle and second nozzle;

forming a second conductive pattern by applying a drop of the liquid composition to the

second selected portion from the second nozzle after irradiating the second selected portion with plasma;

forming a second mask pattern of a resist over the second conductive pattern; and

forming a second wiring by etching the second conductive pattern using the second mask pattern.

24. (Currently amended) A pattern forming method according to claim 23, wherein the gas is selected from the group consisting of He, Ne, Ar, Kr, Xe, oxygen, nitrogen and a combination thereof.

25. (Previously presented) A pattern forming method according to claim 23 wherein the mask pattern is formed by selectively applying the resist to the conductive pattern through a nozzle.

26. (Currently amended) A pattern forming method comprising:

horizontally moving a first nozzle and a second nozzle, which are integrated, to a first selected portion of a surface with a spacing between the integrated first nozzle and second nozzle, and the surface;

~~forming a groove in the selected portion of the surface by selectively treating the surface with plasma of a gas from the first nozzle; and~~

selectively irradiating the first selected portion with plasma of a gas from the first nozzle to form a first groove in the first selected portion of the surface after the step of horizontally moving the integrated first nozzle and second nozzle;

forming a first conductive pattern by applying a liquid drop composition comprising a conductive material to the first groove from the second nozzle after irradiating the first selected portion with plasma;

forming a first mask pattern of a resist over the first conductive pattern after forming the first conductive pattern; [[and]]

forming a first wiring by etching the first conductive pattern using the first mask pattern;

horizontally moving the integrated first nozzle and second nozzle to a second selected portion of a surface with a spacing between the integrated first nozzle and second nozzle, and the surface, after forming the first wiring;

selectively irradiating the second selected portion with plasma of a gas from the first nozzle to form a second groove in the first selected portion of the surface after the step of horizontally moving the integrated first nozzle and second nozzle;

forming a second conductive pattern by applying a liquid drop composition comprising a conductive material to the second groove from the second nozzle after irradiating the second selected portion with plasma;

forming a second mask pattern of a resist over the second conductive pattern after forming the second conductive pattern; and

forming a second wiring by etching the second conductive pattern using the second mask pattern.

27. (Previously Presented) A pattern forming method according to claim 26 wherein the gas is selected from hydrogen, CF_4, NF_3, SF_6, oxygen and a combination thereof.

28. (Previously Presented) A pattern forming method according to claim 26 wherein the mask pattern is formed by selectively applying the resist to the conductive pattern through a nozzle.

29. (Previously Presented) A pattern forming method according to claim 1, wherein the application of the liquid composition is performed at a pressure in a range of 1.3×10^1 to 1.31×10^5 Pa.

30. (Previously Presented) A pattern forming method according to claim 2, wherein the application of the liquid composition is performed at a pressure in a range of 1.3×10^1 to 1.31×10^5 Pa.